

Features

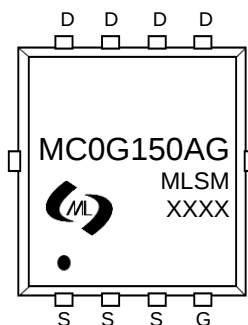
- Split gate trench MOSFET technology
- High density cell design for ultra low RDS(ON)
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Load Switch

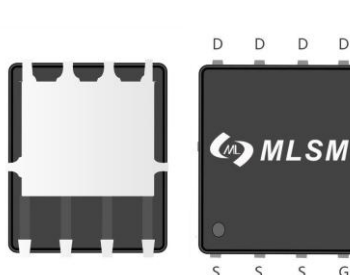
Product Summary

V _{DS}	R _{DS(ON)} TYP	I _D
60V	2.2mΩ@10V	150A
	3.0mΩ@4.5V	

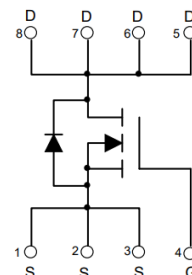


MC0G150AG: Device code
XXXX : Code

Marking and pin assignment



PDFN5X6-8L view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		60	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	150	A

Mounted on Large Heat Sink

I _{DM}	Pulse Drain Current Tested	Tc=25°C	600	A
I _D	Continuous Drain Current	Tc=25°C	150	A
P _D	Maximum Power Dissipation	Tc=25°C	113	W
R _{θJA}	Thermal Resistance Junction-to-Ambient		40	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MC0G150AG	PDFN5X6-8L	MC0G150AG	5,000	10,000	70,000	13"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	--	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	2.2	2.8	mΩ
		V _{GS} =4.5V, I _D =15A	--	3.0	4.0	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	--	4320	--	pF
C _{OSS}	Output Capacitance		--	1510	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	55	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	--	71	--	nC
Q _{gs}	Gate Source Charge		--	17	--	nC
Q _{gd}	Gate Drain Charge		--	11	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, I _D =20A, V _{GS} =10V, R _G =3Ω	--	15	--	nS
t _r	Turn-on Rise Time		--	47	--	nS
t _{d(off)}	Turn-Off Delay Time		--	53	--	nS
t _f	Turn-Off Fall Time		--	19	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=10A	--	--	1.2	V

Typical Operating Characteristics

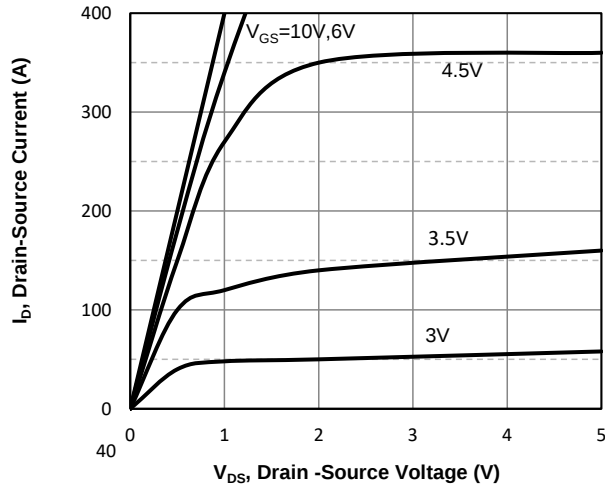


Fig1. Typical Output Characteristics

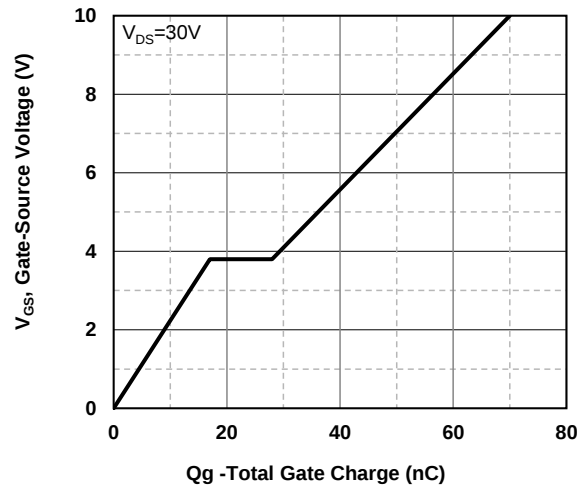


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

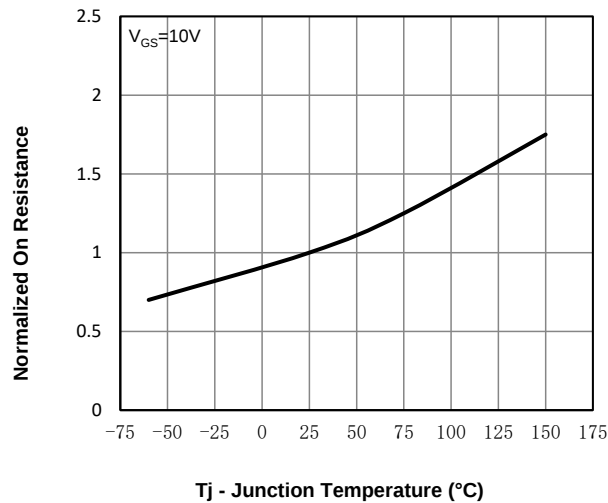


Fig3. Normalized On-Resistance Vs. Temperature

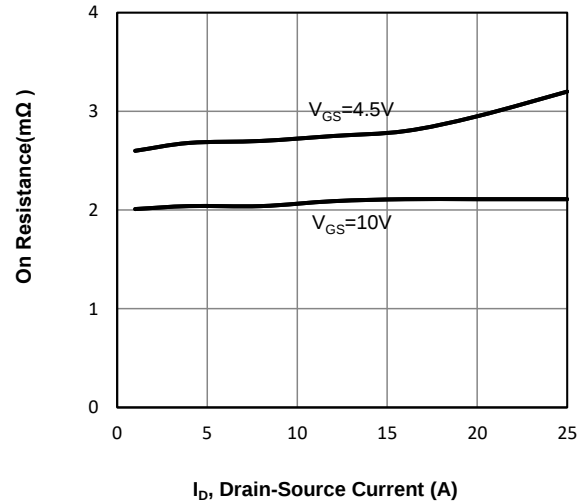


Fig4. On-Resistance Vs. Drain-Source Current

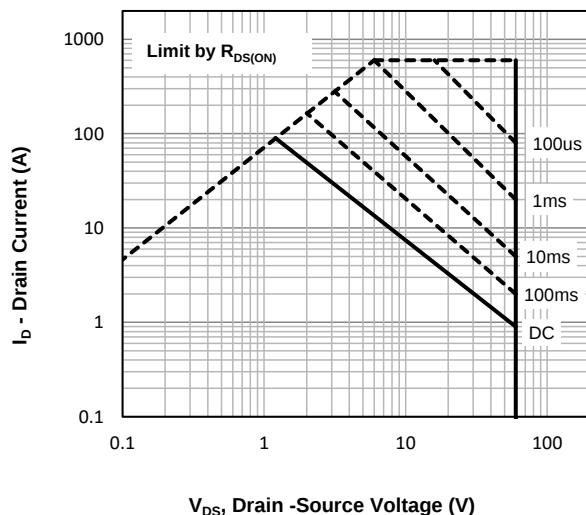


Fig5. Maximum Safe Operating Area

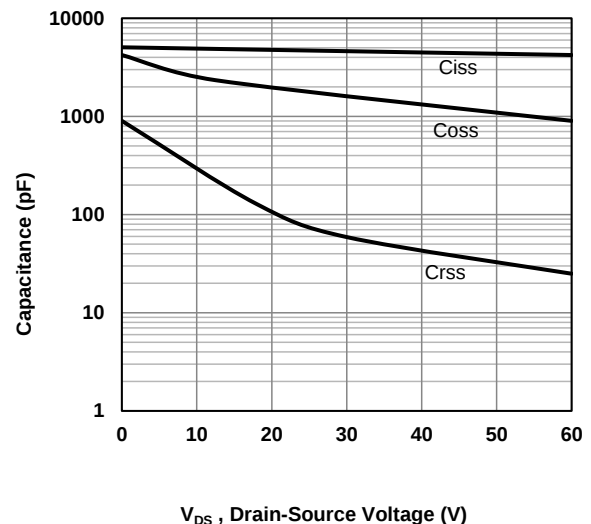
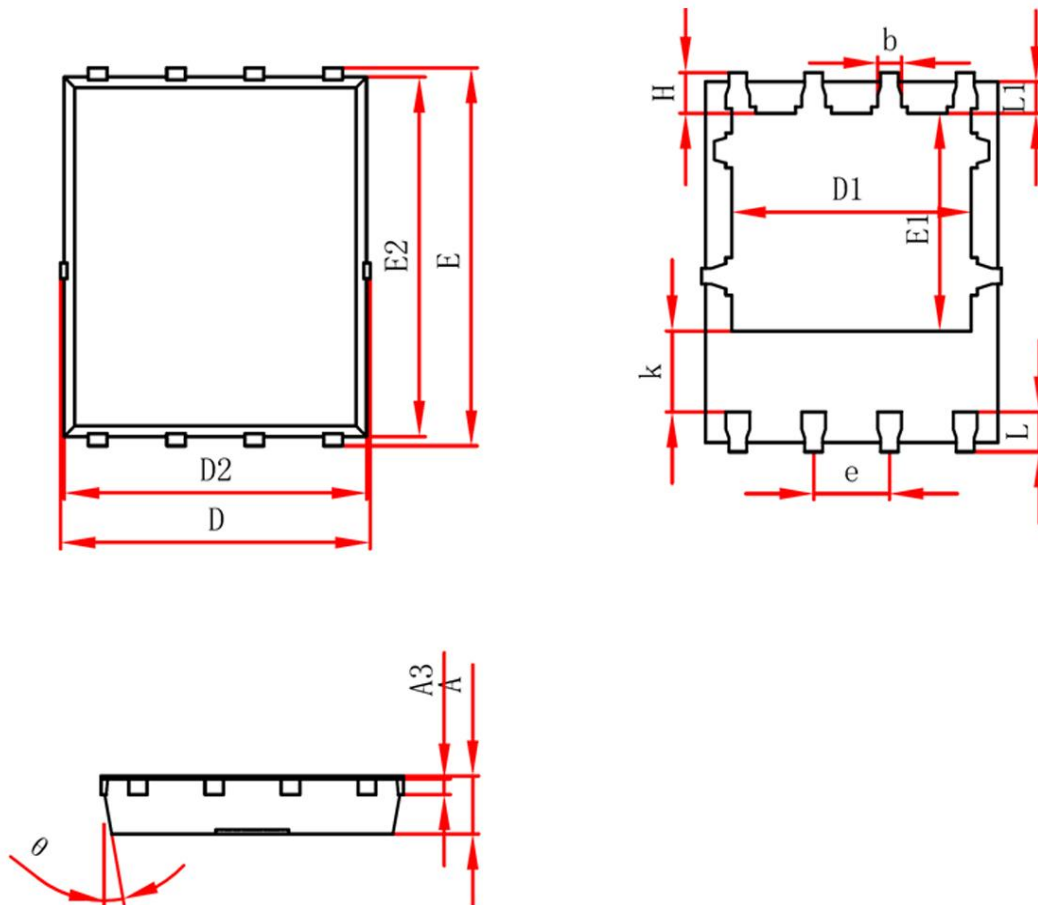


Fig6. Typical Capacitance Vs. Drain-Source

PDFN5X6-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.950	1.050	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.950	5.050	0.196	0.200
E	5.950	6.050	0.235	0.239
D1	4.026	4.126	0.159	0.163
E1	3.510	3.610	0.139	0.143
D2	4.850	4.950	0.192	0.196
E2	5.700	5.800	0.225	0.229
k	1.190	1.390	0.047	0.055
b	0.300	0.400	0.012	0.016
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°